An Optimized SPAD Equivalent-Circuit Model



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✓ GSG samples for precise parameter extraction

S11











S12

<u>S-parameters vary</u> by device and accurately reflect device performance characteristics !



10⁻¹¹ 20 10 15 V_Cathode (V)

under illuminated conditions

✓ I/V curve measurement results

✓ S-parameter fitting results (left : SPAD #1, Right : SPAD #2) (Measured / Simulation @ $V_{FX} = 3V$)



✓LET measurement results < SPAD #1 > < SPAD #2 >

- This enables analysis and anticipation of component characteristics
- By integrating device parameters, circuit simulations achieve ••• higher precision

✓ Significance of an equivalent-circuit model for **SPADs**